

650V 15A Trench and Field Stop IGBT

DESCRIPTION:

- · High ruggedness performance
- 10µs short circuit capability
- Positive V_{CE(SAT)} temperature coefficient
- · High efficiency for motor control
- · Excellent current sharing in parallel operation
- · RoHS compliant.

TYPICAL APPLICATIONS:

- · Home appliances
- Motor drives
- · General inverter



ITO-220AB

IGBT

MAXIMUM RATINGS (Tvj=25°C unless otherwise specified)

Characteristic	Condition	Symbol	Value	Unit
Collector-Emitter Voltage		V _{CES}	650	V
Continuous collector current	Tc=25°C Tc=100°C	I _{C nom}	30 15	Α
Pulsed collector current	t _P limited by Tvjmax	I _{CM}	60	А
Gate emitter voltage		V_{GE}	±20	V
Short circuit withstand time		t _{sc}	10	us
Power dissipation	Tc=25℃ Tc=100℃	P _{tot}	39 19	W
Temperature under switching conditions		Tvj op	-40~+175	$^{\circ}$ C
Storage temperature		T _{STG}	-55~+150	$^{\circ}\!\mathbb{C}$

THERMAL CHARACTERISTICS

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Characteristic	Condition	Symbol	Max.	Unit
IGBT thermal resistance, junction - case		R _{th(j-C)}	3.8	K/W
Diode thermal resistance, junction - case		R _{th(j-C)}	4.2	K/W
Thermal resistance, junction - ambient		R _{th(j-A)}	50	K/W

ELECTRICAL CHARATERISTICS

Characteristic	Symbol	Min.	Тур.	Max.	Unit
Collector-emitter cut-off current VCE=650V, VGE=0V Tvj=25°C	I _{CES}			50	uA
Gate-emitter leakage current VCE=0V, VGE=20V Tvj=25°C	I _{GES}			100	nA
Gate-Emitter threshold voltage IC=1.0mA, VGE= VCE Tvj=25 $^{\circ}$ C	$V_{GE(th)}$	5.4	5.6	5.9	V
Collector-Emitter saturation voltage VGE=15V, IC=15A Tvj=25℃ VGE=15V, IC=15A Tvj=150℃	V _{CE(SAT)}		1.6 1.9		V
Input capacitance f=1MHz, VCE=30 V, VGE=0 V Tvj=25°C	C _{ies}		1055		pF
Output capacitance f=1MHz, VCE=30 V, VGE=0 V Tvj=25℃	C _{oes}		57		pF
Reverse transfer capacitance f=1MHz, VCE=30 V, VGE=0 V Tvj=25°C	C _{res}		15		pF
Gate charge IC = 15A, VGE = 15 V,VCC =520V Tvj=25°C	Q_{G}		55		nC
Turn-on delay time IC=15A, VCC=400 V	td _(ON)		17 16		ns
Rise time IC=15A, VCC=400 V Tvj=25 $^{\circ}$ C VGE=0/15 V, RG=10 Ω Tvj=150 $^{\circ}$ C (inductive load)	tr		14 15		ns
Turn-off delay time IC=15A, VCC=400 V	td _(OFF)		104 119		ns
Fall time IC=15A, VCC=400 V Tvj=25°C VGE=0/15 V, RG=10 Ω Tvj=150°C (inductive load)	tf		46 81		ns
Turn-on energy IC=15A, VCC=400 V $Tvj=25^{\circ}C$ VGE=0/15 V, RG=10 Ω $Tvj=150^{\circ}C$ (inductive load)	E _(ON)		0.30 0.38		mJ

Turn-off energy loss per pulse IC=15A, VCC=400 V	E _(OFF)		0.27 0.40		mJ
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Diode

MAXIMUM RATINGS (Tvj=25 $^{\circ}$ C unless otherwise specified)

Characteristic	Condition	Symbol	Value	Unit
Repetitive peak reverse voltage	Tvj=25℃	V_{RRM}	650	V
Continuous forward current	Tc=100°C	I _F	15	Α
Diode maximum current	t _P limited by Tvj max	I _{FM}	60	Α

ELECTRICAL CHARATERISTICS

Characteristic	Symbol	Min.	Тур.	Max.	Unit
Forward voltage IF=15A, VGE=0 V Tvj=25°C IF=15A, VGE=0 V Tvj=150°C	V _F		1.4 1.2		V
Reverse Recovered Time IF=15 A, Tvj=25°C -diF/dt =600A/µs Tvj=150°C VR=400 V	T _{rr}		55 75		ns
Peak reverse recovery current IF=15 A, Tvj=25°C -diF/dt =600A/µs Tvj=150°C VR=400 V	I _{RRM}		9.5 15		А
Reverse Recovered charge IF=15 A, Tvj=25°C -diF/dt =600A/µs Tvj=150°C VR=400 V	Q _{rr}		220 450		nC

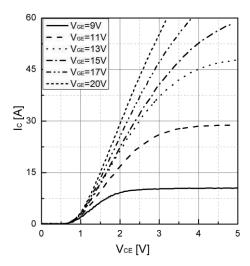


Figure 1. Typical output characteristics (Tvj=25 $^{\circ}\text{C}$)

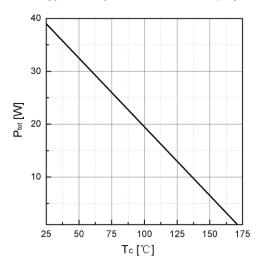


Figure 3. Power dissipation as a function of TC

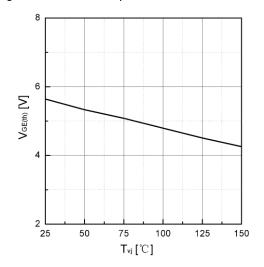


Figure 5. Typical VGE(th) as a function of Tvj $(I_C=1mA)$

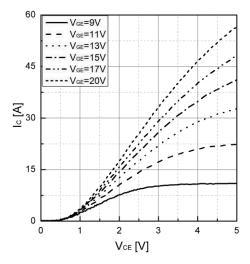


Figure 2. Typical output characteristics (Tvj=175°C)

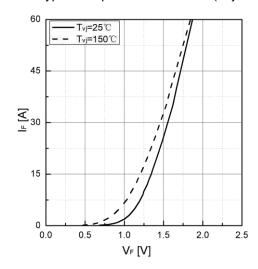


Figure 4. Typical IF as a function of VF

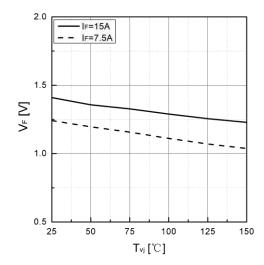


Figure 6. Typical VF as a function of Tvj

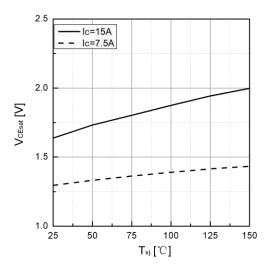


Figure 7. Typical VCEsat as a function of Tvj

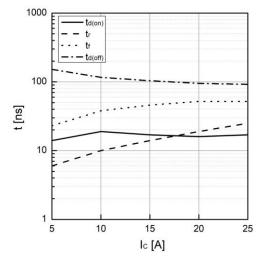


Figure 9. Typical switching times as a function of IC

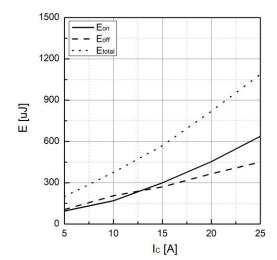


Figure 11. Typical switching energy losses as a function of IC

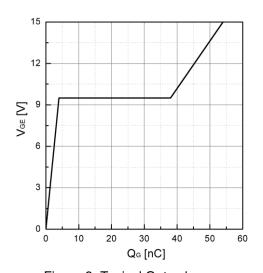


Figure 8. Typical Gate charge

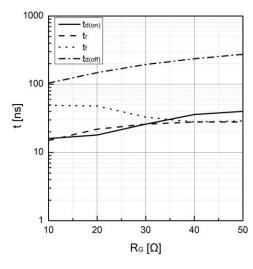


Figure 10. Typical switching times as a function of RG

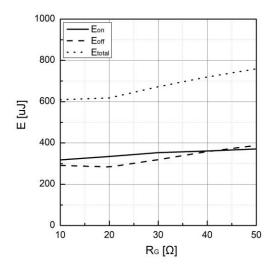


Figure 12. Typical switching energy losses as a function of RG

RA-D-1633 Ver.A

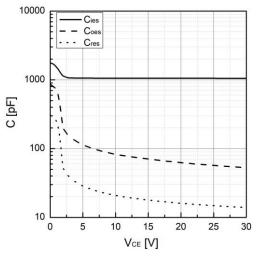


Figure 13. Typical capacitance as a function of VCE (f=1Mhz, VGE=0V)

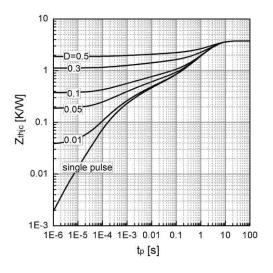
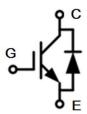
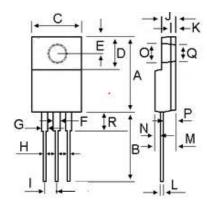


Figure 14. Transient thermal impedance, IGBT

· Circuit diagram



• Package outlines : Dimensions in (mm)



DIM	MILLIMETERS		
DIIVI	MIN	MAX	
Α	14.80	16.10	
B C	12.65	14.40	
С	9.70	10.36	
D E F	4.60	6.80	
Е	2.50	3.50	
F	0.90	1.55	
G	0.90	1.55	
Η	0.50	0.90	
	2.40	2.70	
J	2.34	3.30	
K	0.55	1.30	
┙	0.36	0.80	
М	4.20	4.90	
N	1.10	1.80	
0	2.90	3.50	
Р	2.30	3.15	
Q	2.90	3.50	
R	2.80	4.85	



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